

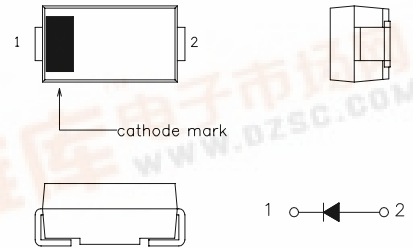


DIODE Type : EC10DS1

FEATURES

- * Miniature Size, Surface Mount Device
- * High Surge Capability
- * Low Forward Voltage Drop
- * Low Reverse Leakage Current
- * Packaged in 12mm Tape and Reel
- * Not Rolling During Assembly

OUTLINE DRAWING



Maximum Ratings

Approx Net Weight: 0.06g

Rating	Symbol	EC10DS1		Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100		V
Non-repetitive Peak Reverse Voltage	V_{RSM}	250		V
Average Rectified Output Current	I_O	0.74	Ta=25 °C *1	50Hz Half Sine Wave Resistive Load
		1.0	Ta=25 °C *2	
RMS Forward Current	$I_{F(RMS)}$	1.57		A
Surge Forward Current	I_{FSM}	25	50Hz Half Sine Wave, 1cycle Non-repetitive	A
Operating Junction Temperature Range	T_{jw}	-40 to +150		°C
Storage Temperature Range	T_{stg}	-40 to +150		°C

Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I_{RM}	$T_j = 25^\circ\text{C}, V_{RM} = V_{RRM}$	-	-	10	μA
Peak Forward Voltage	V_{FM}	$T_j = 25^\circ\text{C}, I_{FM} = 1.0\text{A}$	-	-	1.1	V
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	*1	-	157	°C /W
			*2	-	108	

*1 Glass Epoxy Substrate Mounted (Soldering Lands=2x2mm, Both Sides)

*2 Alumina Substrate Mounted (Soldering Lands=2x2mm, Both Sides)



EC10DS1 OUTLINE DRAWING (Dimensions in mm)

